

Page 12, line 3, change "preferably" to --which may be--.

Page 12, line 32, change "a manner that is" to --an available manner.--.

Page 12, line 33, delete "known per se."

Page 12, line 33, delete "a".

Page 12, delete line 34, and insert --an available manner to ensure the stability of--.

IN THE ABSTRACT:

Delete lines 1 to 14, and insert:

ABSTRACT OF THE DISCLOSURE

A method for eliminating eruptions, impurities, and/or damage in a crystal lattice by selectively etching silicon elements of surface-plated and sawn-out parts of a silicon wafer. At least areas of the silicon elements are brought into contact with a gaseous etching medium that etches silicon selectively in a chemical reaction, and gaseous reaction products are produced during etching. An interhalogen or fluorine-noble gas compound that is in a gaseous state or was converted to the gaseous phase may be used as the etching medium. The method is believed to be suitable for producing power diodes sawn from a wafer or for overetching fully mounted individual diodes.

IN THE CLAIMS:

On the first page of the claims, first line, change "Patent Claims" to:

--WHAT IS CLAIMED IS:--.

Please cancel original claims 1 to 15, without prejudice, and please add new claims 16 to 30 as follows:

--16. (New) A method for substantially eliminating at least one of eruptions, impurities and damage in a crystal lattice consisting of:

selectively etching at least one silicon element of the surface-plated, sawn-out part of the silicon wafer by bringing at least an area of the at least one silicon